

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

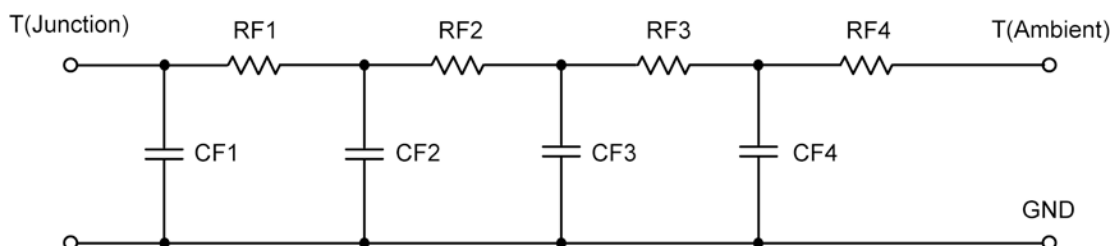
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	14.1987	N/A	1.4338
RT2	15.6302	N/A	7.7779
RT3	7.2391	N/A	2.0581
RT4	37.0637	N/A	8.7302
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	9.1933 m	N/A	879.1230 u
CT2	1.3008 m	N/A	3.4305 m
CT3	1.1522	N/A	66.0593 m
CT4	1.8243	N/A	2.6871 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	14.4487	N/A	4.4270
RF2	13.0397	N/A	9.2285
RF3	14.2175	N/A	5.2678
RF4	30.2941	N/A	1.0767
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.0284 m	N/A	645.9204 u
CF2	6.0241 m	N/A	999.2337 u
CF3	580.7078 m	N/A	404.2747 u
CF4	1.4614	N/A	188.9370 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

